

LAPT

2SA1215

Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC2921)

Application : Audio and General Purpose

■Absolute maximum ratings (Ta=25°C)

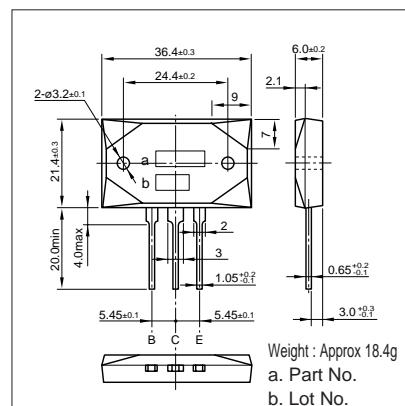
Symbol	Ratings	Unit
V _{CBO}	-160	V
V _{CEO}	-160	V
V _{EBO}	-5	V
I _c	-15	A
I _b	-4	A
P _c	150(Tc=25°C)	W
T _j	150	°C
T _{tsg}	-55 to +150	°C

■Electrical Characteristics (Ta=25°C)

Symbol	Conditions	Ratings	Unit
I _{CBO}	V _{CB} =-160V	-100max	μA
I _{EBO}	V _{EB} =-5V	-100max	μA
V _{(BR)CEO}	I _c =-25mA	-160min	V
h _{FE}	V _{CE} =-4V, I _c =-5A	50min*	
V _{CE(sat)}	I _c =-5A, I _b =-0.5A	-2.0max	V
f _r	V _{CE} =-12V, I _e =2A	50typ	MHz
C _{OB}	V _{CB} =-10V, f=1MHz	400typ	pF

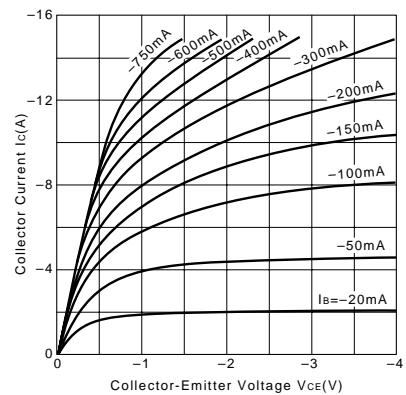
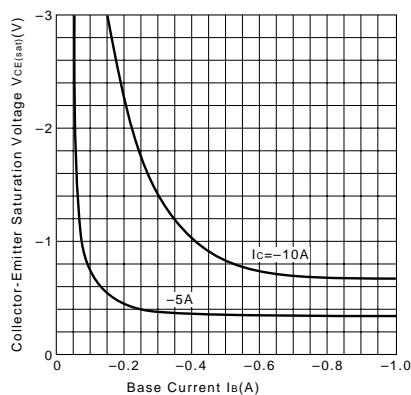
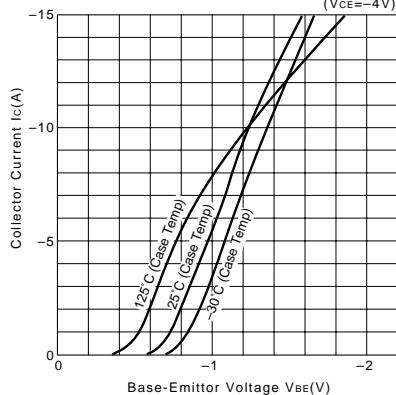
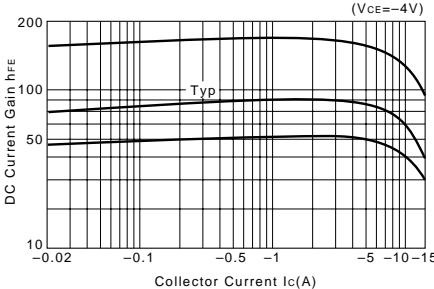
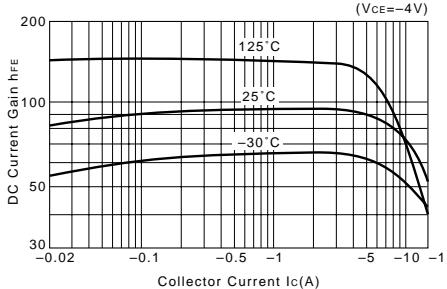
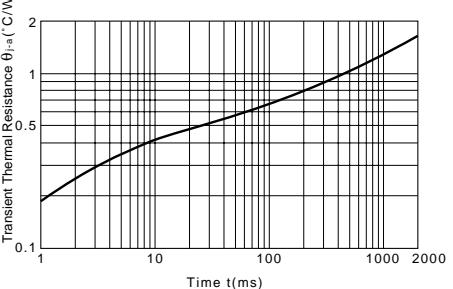
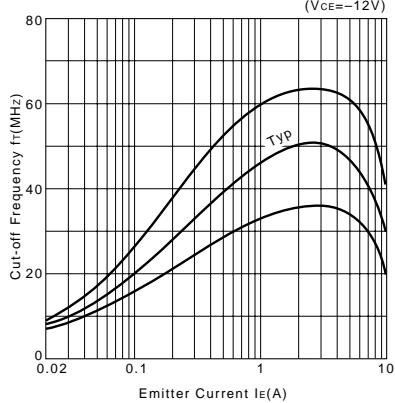
*h_{FE} Rank O(50to100), P(70to140), Y(90to180)

External Dimensions MT-200

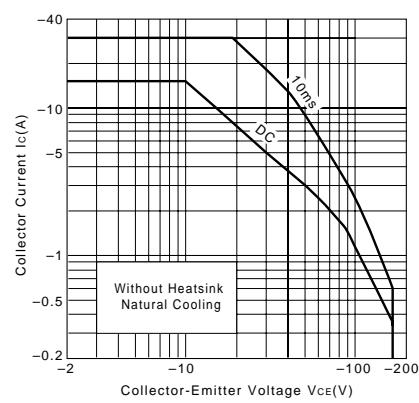


■Typical Switching Characteristics (Common Emitter)

V _{cc} (V)	R _L (Ω)	I _c (A)	V _{B2} (V)	I _{b1} (mA)	I _{b2} (mA)	t _{on} (μs)	t _{tsg} (μs)	t _f (μs)
-60	12	-5	5	-500	500	0.25typ	0.85typ	0.2typ

I_c-V_{CE} Characteristics (Typical)V_{CE(sat)}-I_b Characteristics (Typical)I_c-V_{BE} Temperature Characteristics (Typical)h_{FE}-I_c Characteristics (Typical)h_{FE}-I_c Temperature Characteristics (Typical)θ_{j-a}-t Characteristicsf_r-I_e Characteristics (Typical)

Safe Operating Area (Single Pulse)

P_c-Ta Derating